











TPD8E003

SLLSE38B-JUNE 2010-REVISED MARCH 2016

TPD8E003 8-Channel ESD Protection Diode for Keypad and GPIO

Features

- IEC 61000-4-2 Level 4 ESD Protection
 - ±12-kV Contact Discharge
 - ±15-kV Air-Gap Discharge
- IEC 61000-4-5 Surge Protection
 - 3.5-A (8/20 µs)
- IO Capacitance: 9 pF (Typical)
- DC Breakdown Voltage: 6 V (Minimum)
- Low Leakage Current: 100 nA (Maximum)
- Industrial Temperature Range: -40°C to 85°C
- Space-Saving, Ultra-Thin, WSON Package

Applications

- **End Equipment**
 - Laptops and Desktops
 - IP Phones
- Interfaces
 - Keypads
 - **GPIO Headers**
 - **Touchscreens**
 - Low-Speed Memory Interfaces

3 Description

The TPD8E003 device is a unidirectional Transient Voltage Suppressor (TVS) based Electrostatic Discharge (ESD) protection diode array. The TPD8E003 is rated to dissipate ESD strikes above the maximum level specified in the IEC 61000-4-2 international standard (Level 4). This device provides 8 channels of ESD protection in a space-saving WSON package. Typical applications for the Keypad, TPD8E003 include GPIO, touchscreen, and low-speed memory interfaces. Also, see the TPD2E2U06 and TPD4E05U06 for 2- and 4-channel ESD protection solutions, respectively.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPD8E003	WSON (8)	1.70 mm × 1.35 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Circuit Schematic

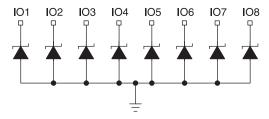






Table of Contents

1	Features 1		7.3 Feature Description
2	Applications 1		7.4 Device Functional Modes
3	Description 1	8	Application and Implementation
4	4 Revision History2		8.1 Application Information
5			8.2 Typical Application
6	Specifications4	9	Power Supply Recommendations
•	6.1 Absolute Maximum Ratings	10	Layout
	6.2 ESD Ratings		10.1 Layout Guidelines
	6.3 ESD Ratings – Surge Protection		10.2 Layout Example
	6.4 Recommended Operating Conditions	11	Device and Documentation Support 1
	6.5 Thermal Information		11.1 Community Resources
	6.6 Electrical Characteristics5		11.2 Trademarks 1
	6.7 Typical Characteristics		11.3 Electrostatic Discharge Caution 1
7	Detailed Description 6		11.4 Glossary1
-	7.1 Overview	12	Mechanical, Packaging, and Orderable
	7.2 Functional Block Diagram 6		Information 1

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

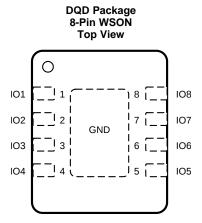
Changes from Revision A (September 2010) to Revision B

Page

- Added ESD Ratings tables, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.



5 Pin Configuration and Functions



Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION			
NO.	NAME	ITPE	DESCRIPTION			
1	IO1	I/O	ESD protected channel			
2	IO2	I/O	ESD protected channel			
3	IO3	I/O	ESD protected channel			
4	IO4	I/O	ESD protected channel			
5	IO5	I/O	ESD protected channel			
6	IO6	I/O	ESD protected channel			
7	IO7	I/O	ESD protected channel			
8	IO8	I/O	ESD protected channel			
GND	GND	G	Connect to ground			

(1) G = Ground, I = Input, O = Output



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
	IO voltage tolerance (IO pins)		6	V
	Peak pulse power (tp = 8/20 μs)		55	W
	Peak pulse current (tp = 8/20 μs)		3.5	Α
T _A	Operating free-air temperature	-40	85	°C
T _{stg}	Storage temperature	– 55	155	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
.,		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	.,
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 ESD Ratings - Surge Protection

			VALUE	UNIT
\/	Electrostatio discharge	IEC 61000-4-2 contact discharge	±12000	V
V _(ESD)	Electrostatic discharge	IEC 61000-4-2 air-gap discharge	±15000	V

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V_{IO}	Input pin voltage	0	5.5	V
T _A	Operating free-air temperature	-40	85	°C

6.5 Thermal Information

		TPD8E003	
	THERMAL METRIC ⁽¹⁾	DQD (WSON)	UNIT
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	98.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	110.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	42.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	42.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	22.0	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

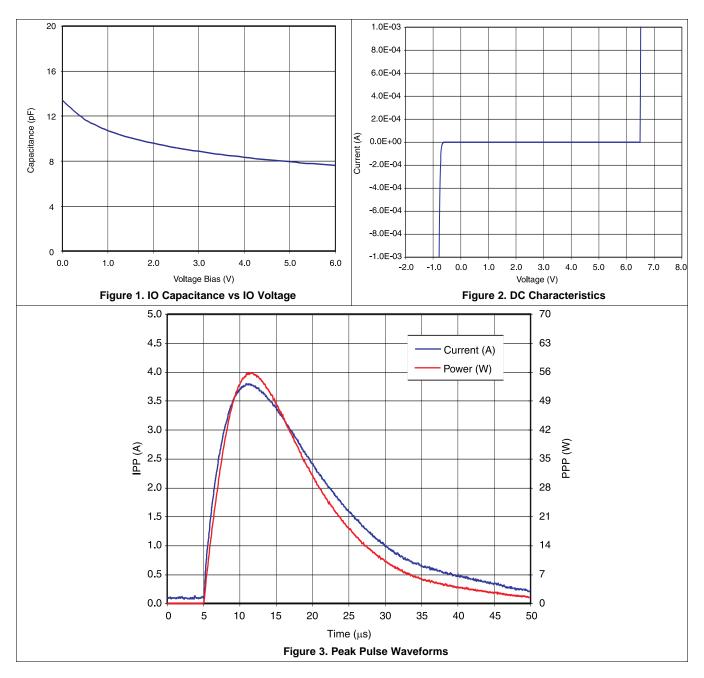


6.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
V_{clamp}	Clamp voltage	$I_{IO} = 2 \text{ A}$, IO pin-to-ground			10	V
II	Leakage current	IO pin-to-ground			0.1	μΑ
C _{IO}	IO capacitance	$V_{IO} = 2.5 \text{ V}$, IO pins	7	9	12	рF
ΔC_{IO}	Differential line capacitance	V _{IO} = 2.5 V, between IO pins		0.1		рF
V_{BR}	Break-down voltage	$I_{IO} = 1 \text{ mA}$	6			V
R _{dyn}	Dynamic resistance	$I_{IO} = 1$ A, between IO pin and ground		1		Ω

6.7 Typical Characteristics



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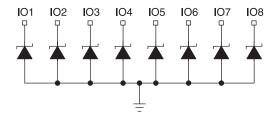
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7 Detailed Description

7.1 Overview

The TPD8E003 is a unidirectional TVS-based, ESD protection diode array. The TPD8E003 is rated to dissipate ESD strikes above the maximum level specified in the IEC 61000-4-2 international standard (Level 4). This device provides 8 channels of ESD protection in a space-saving WSON package.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 IEC 61000-4-2 ESD Protection

The I/O pins can withstand ESD events up to ±12-kV contact and ±15-kV air gap. An ESD/surge clamp diverts the current to ground.

7.3.2 IEC 61000-4-5 Surge Protection

The I/O pins can withstand surge events up to 3.5 A and 55 W (8/20 µs waveform). An ESD/surge clamp diverts this current to ground.

7.3.3 IO Capacitance

The capacitance between each I/O pin-to-ground is 9 pF (typical) and 12 pF (maximum).

7.3.4 DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is a minimum of 6 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of 5.5 V.

7.3.5 Low Leakage Current

The I/O pins feature an low leakage current of 100 nA (maximum) with a bias of 2.5 V.

7.3.6 Industrial Temperature Range

This device features an industrial operating range of -40°C to 85°C.

7.3.7 Space-Saving Package

This device features a space-saving WSON package that puts many channels of ESD in a small form factor.

7.4 Device Functional Modes

TPD8E003 is a passive integrated circuit that triggers when voltages are above V_{BR} or below the lower diodes V_f (-0.6 V). During ESD events, voltages as high as ± 15 kV (air) can be directed to ground through the internal diode network. When the voltages on the protected line fall below the trigger levels of TPD8E003 (usually within 10s of nano-seconds) the device reverts to passive.



8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPD8E003 offers eight ESD clamp circuits in a space-saving DQD package. When placed near the connector, the TPD8E003 ESD solution offers little or no signal distortion during normal operation due to low IO capacitance and ultra-low leakage current specifications. The TPD8E003 ensures that the core circuitry is protected and the system is functioning properly in the event of an ESD strike.

8.2 Typical Application

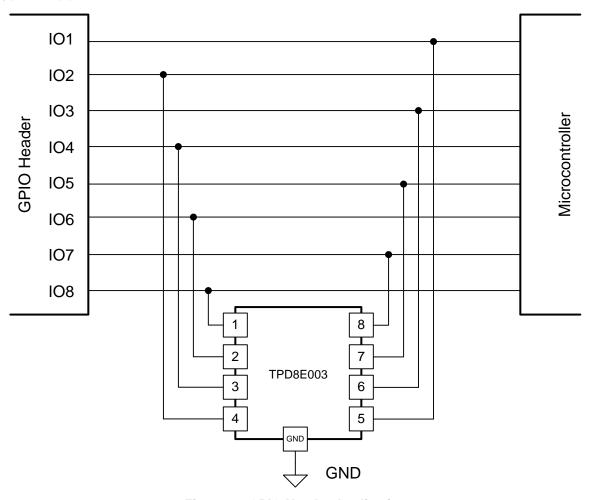


Figure 4. GPIO Header Application

8.2.1 Design Requirements

For this design example, one TPD8E003 is used to protect an 8-pin GPIO header.

Given the example application, the parameters listed in Table 1 are known.



Table 1. Design Parameters

PARAMETER	VALUE
Signal Range on Protected Lines	0 V to 5 V
Required Level of IEC ESD Protection	±8kV Contact, ±15kV Air Gap

8.2.2 Detailed Design Procedure

To begin the design process, some parameters must be decided upon; the designer must know the following:

- · Voltage range of the signal on all protected lines
- Required ESD protection needed

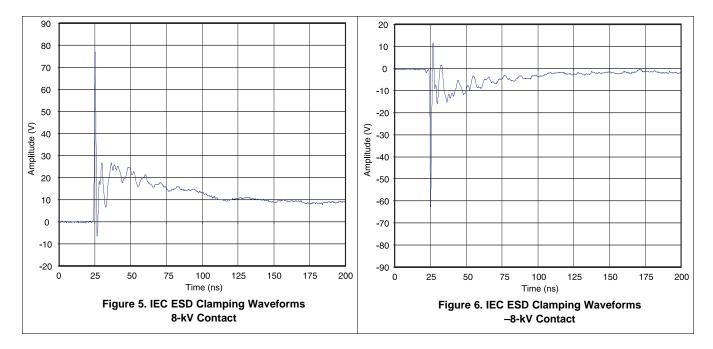
8.2.2.1 Signal Range

The TPD8E003 supports signal ranges between 0 V and 5.5 V, which supports the GPIO application.

8.2.2.2 Required ESD Protection

The TPD8E003 is rated to withstand up to ± 12 -kV contact and ± 15 -kV air gap IEC ESD. This meets the IEC ESD design target with room to spare.

8.2.3 Application Curves





9 Power Supply Recommendations

This device is a passive ESD protection device and there is no need to power it. Take care making sure that the maximum voltage specifications for each line are not violated.

10 Layout

10.1 Layout Guidelines

For proper operation of the ESD clamps, both during normal function and ESD events, the following layout and design guidelines must be followed:

- Place the TPD8E003 solution close to the connector. This allows the TPD8E003 to take away the energy associated with ESD strike before it reaches the internal circuitry of the system board.
- TI recommends employing two signal layers in the printed-circuit board (PCB) to route through the eight ESD clamp terminals of the TPD8E003.
- Ensure that there is proper metallization for the GND vertical interconnect access (VIA). During an ESD
 event, the in-rush current flows to the system GND plane through the GND VIA. Having a low-impedance
 path allows the current to flow quickly to GND, effectively building a robust, system-level ESD immunity.
- · Place the VIA under the DQD pad in locations that offer maximum flexibility in board routing.
- One common set of guidelines (not restricted to all cases):
 - Trace width: 4 mmVIA diameter: 6 mm
 - DQD package pad dimensions: 8 mm x 12 mm

10.2 Layout Example

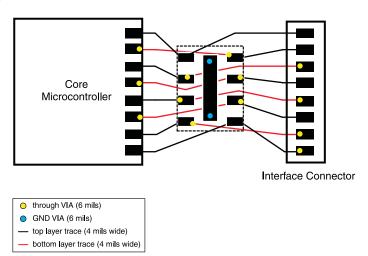
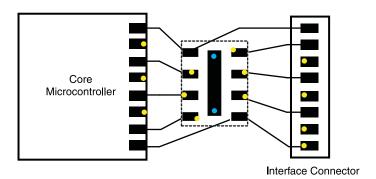


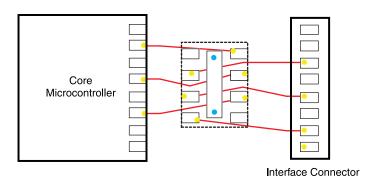
Figure 7. Board Layout With the TPD8E003DQDR



Layout Example (continued)



TOP LAYER ROUTING (INCLUDING VIAs)



BOTTOM LAYER ROUTING (INCLUDING VIAs)



Figure 8. Top and Bottom Layer Board Layout With the TPD8E003DQDR

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11 Device and Documentation Support

11.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.2 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

11.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGE OPTION ADDENDUM

6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
TPD8E003DQDR	ACTIVE	WSON	DQD	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(65S, 65U)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

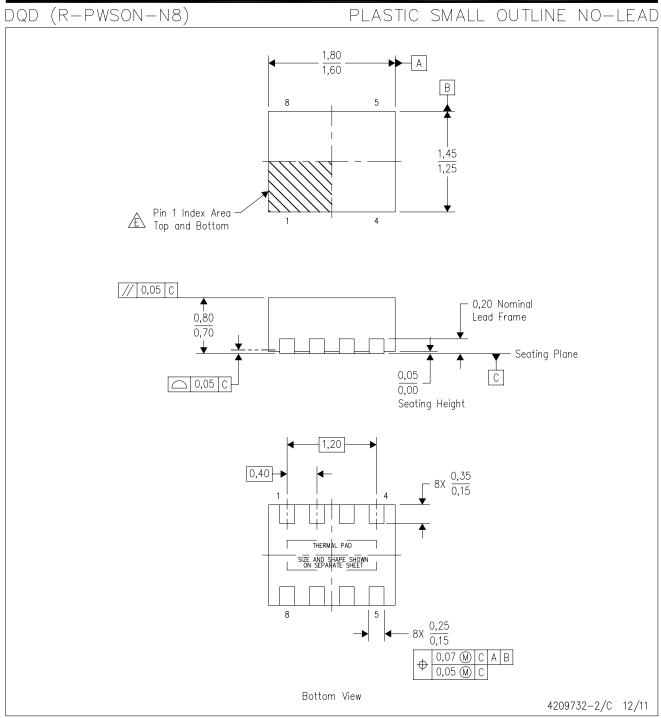
Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD8E003DQDR	WSON	DQD	8	3000	180.0	8.4	1.65	2.0	0.95	4.0	8.0	Q1

www.ti.com 15-Feb-2018



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPD8E003DQDR	WSON	DQD	8	3000	183.0	183.0	20.0



NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- This drawing is subject to change without notice. В.

- SON (Small Outline No-Lead) package configuration.

 The package thermal pad must be soldered to the board for thermal and mechanical performance.

 See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Fin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.



DQD (R-PWSON-N8)

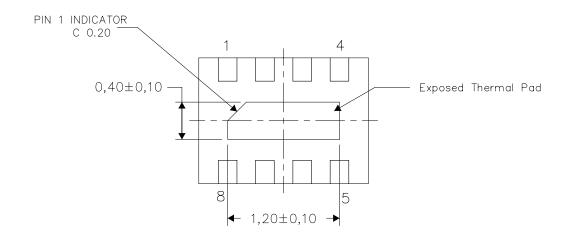
PLASTIC SMALL OUTLINE NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

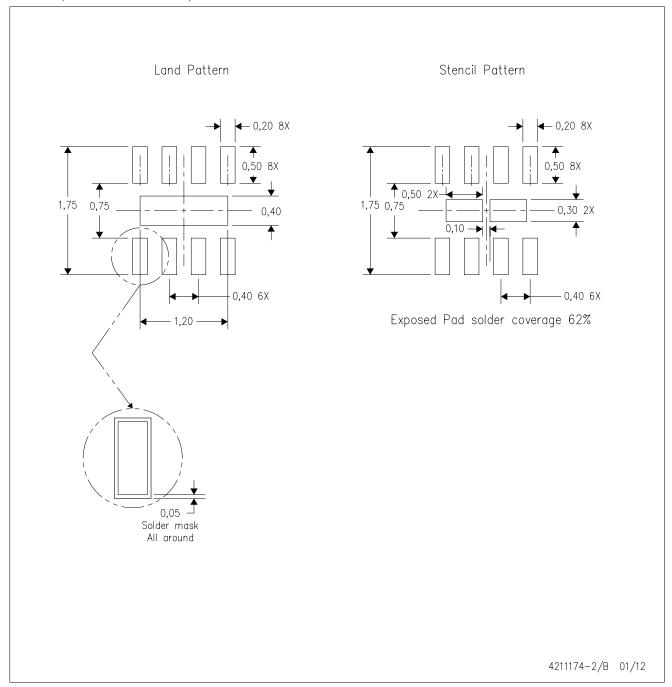
4209733-2/C 12/11

NOTE: All linear dimensions are in millimeters



DQD (R-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
 - E. Maximum stencil thickness 0,1016 mm (4 mils). All linear dimensions are in millimeters.
 - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - G. Side aperture dimensions over—print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



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